



University of Electronic Science and Technology of China

Sub-MicroMachining with Ultrafast Pulse Laser Interference for the Drilling of Microvias

Prof. Yongqi Fu

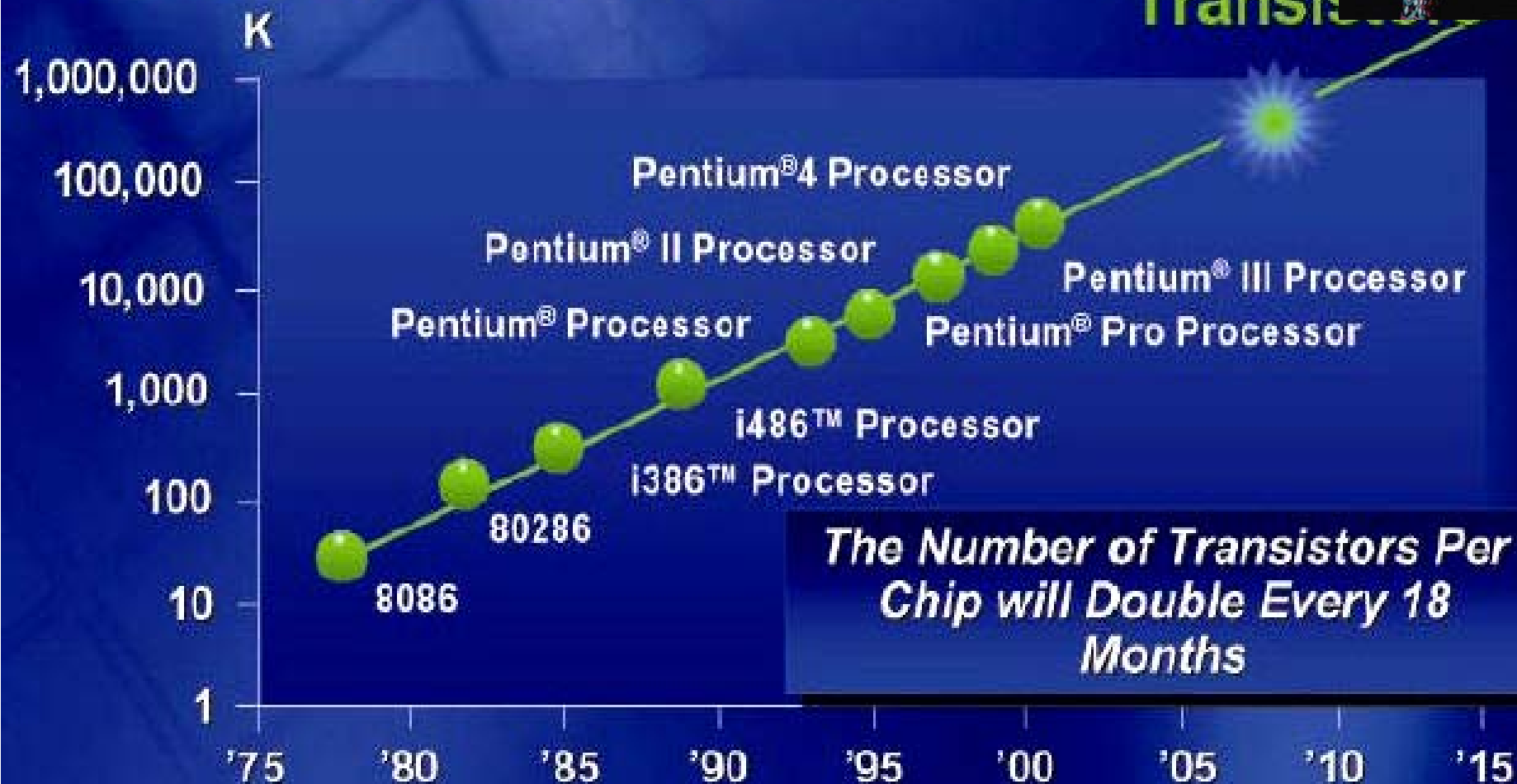
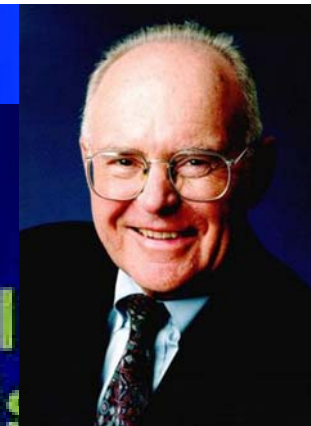
Miniaturization



Miniaturisation

Breaking Barriers to Moore's Law

1 Billion Transistors



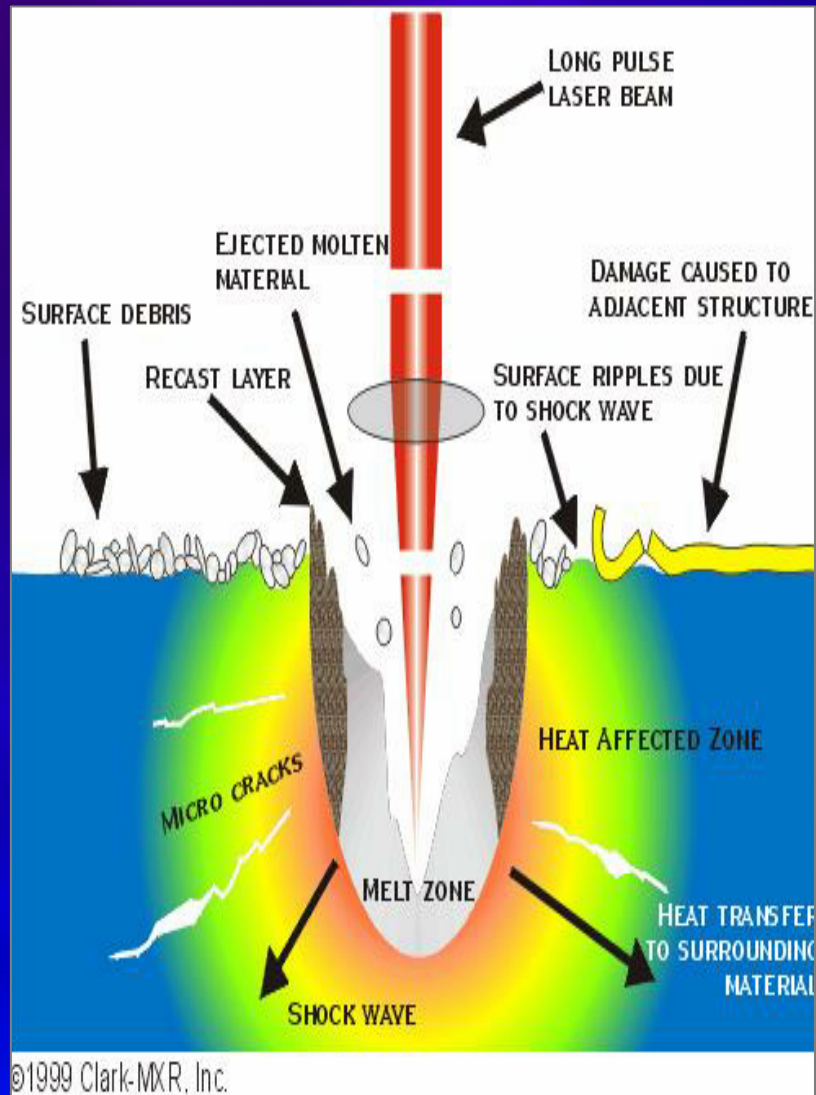
Source: Intel

Ultrafast Laser Sub-spot Ablation Mechanism

- permits the ablation of features smaller than the focal spot size when operated near threshold as only a fraction (the central region) of the focused light will exceed the threshold intensity.
- with a **femtosecond pulsed laser**, it is possible to control that only 1/10 (10%) of the focal spot size will machine.

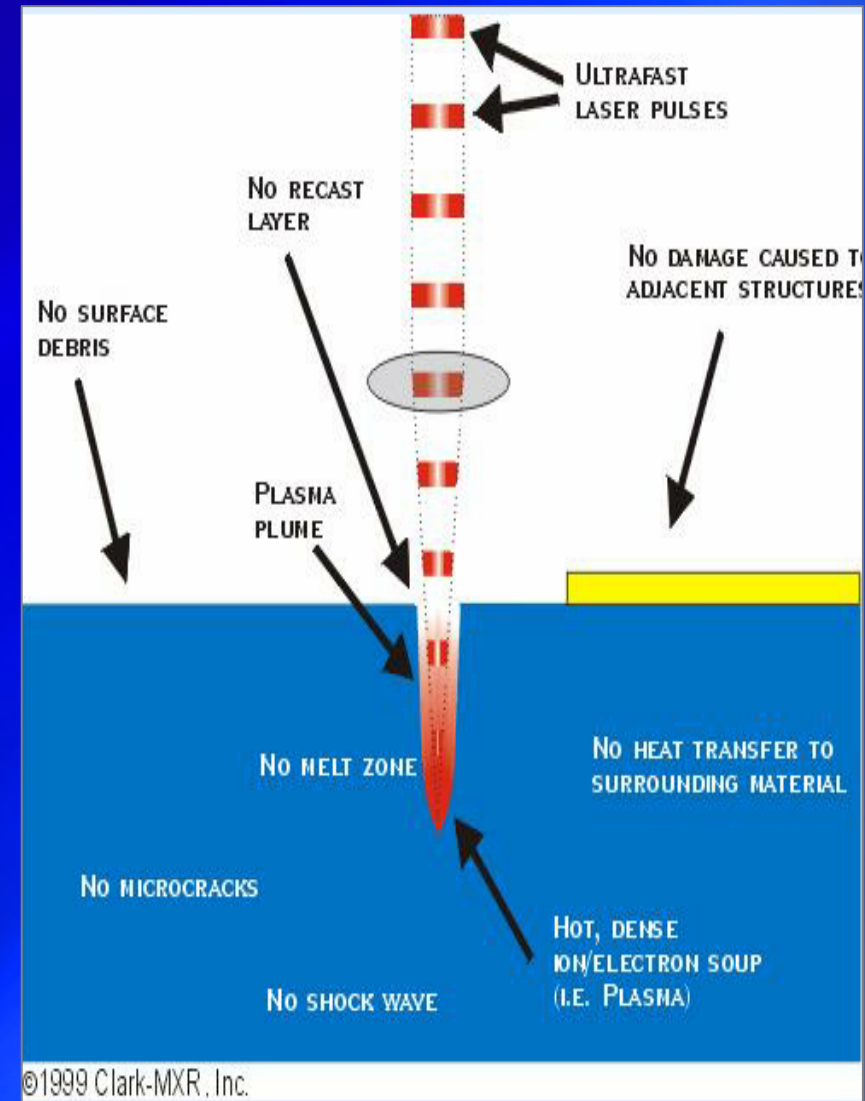
WHY FEMTOSECOND PULSED LASER

Long pulse

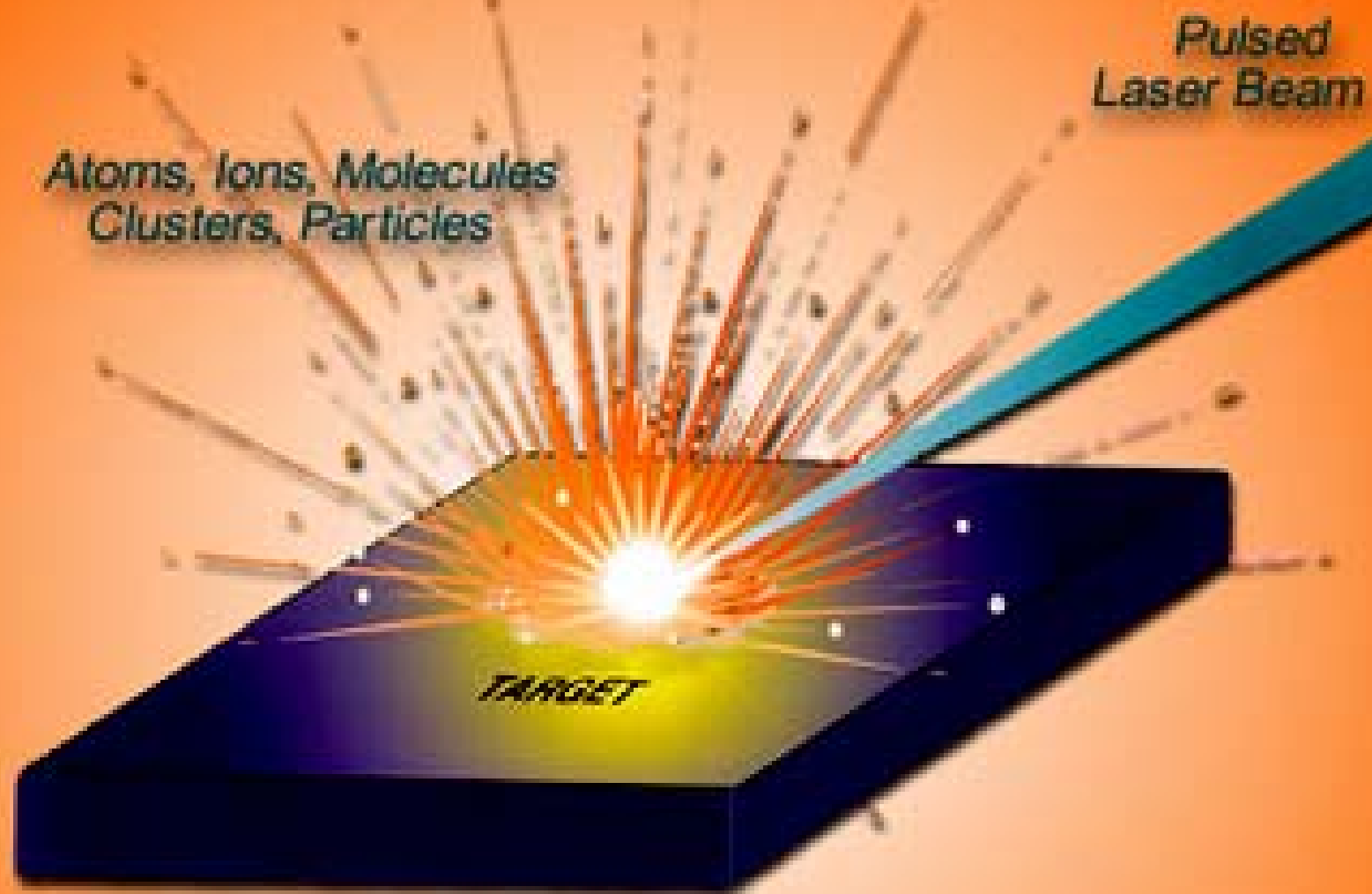


Vs

Ultra short pulse

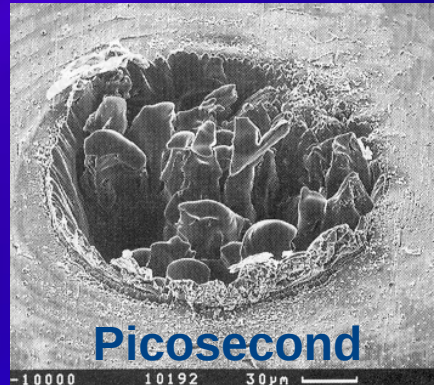


C.W



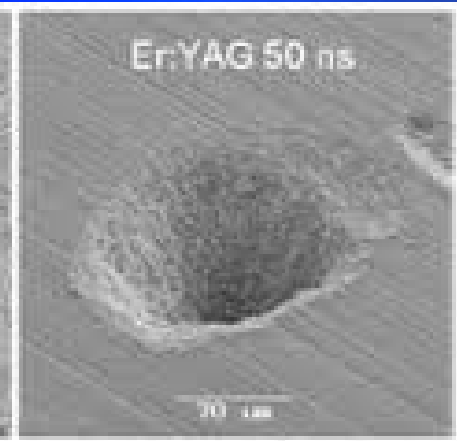
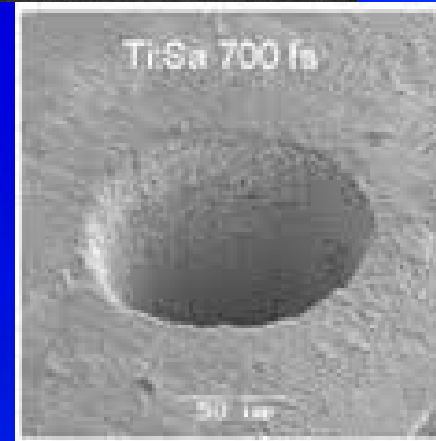
Shock waves

WHY FEMTOSECOND PULSED LASER



M. Carsten et. al., 1996,
Optics Communications

- Can machine any materials
- No melt zone, no microcracks
- Highly reproducible
- Does not affect surrounding material
- Can machine sub-micron features
- Can machine inside transparent materials



Limitation of Current Laser Ablation Technology:

- reached its lowest limit when it hit the 1/10th of the laser focal spot size range
- smallest ablation feature reported is 200 nm [1]
- the smaller the ablation feature size, the more pronounced the problem of tapering & low aspect ratio

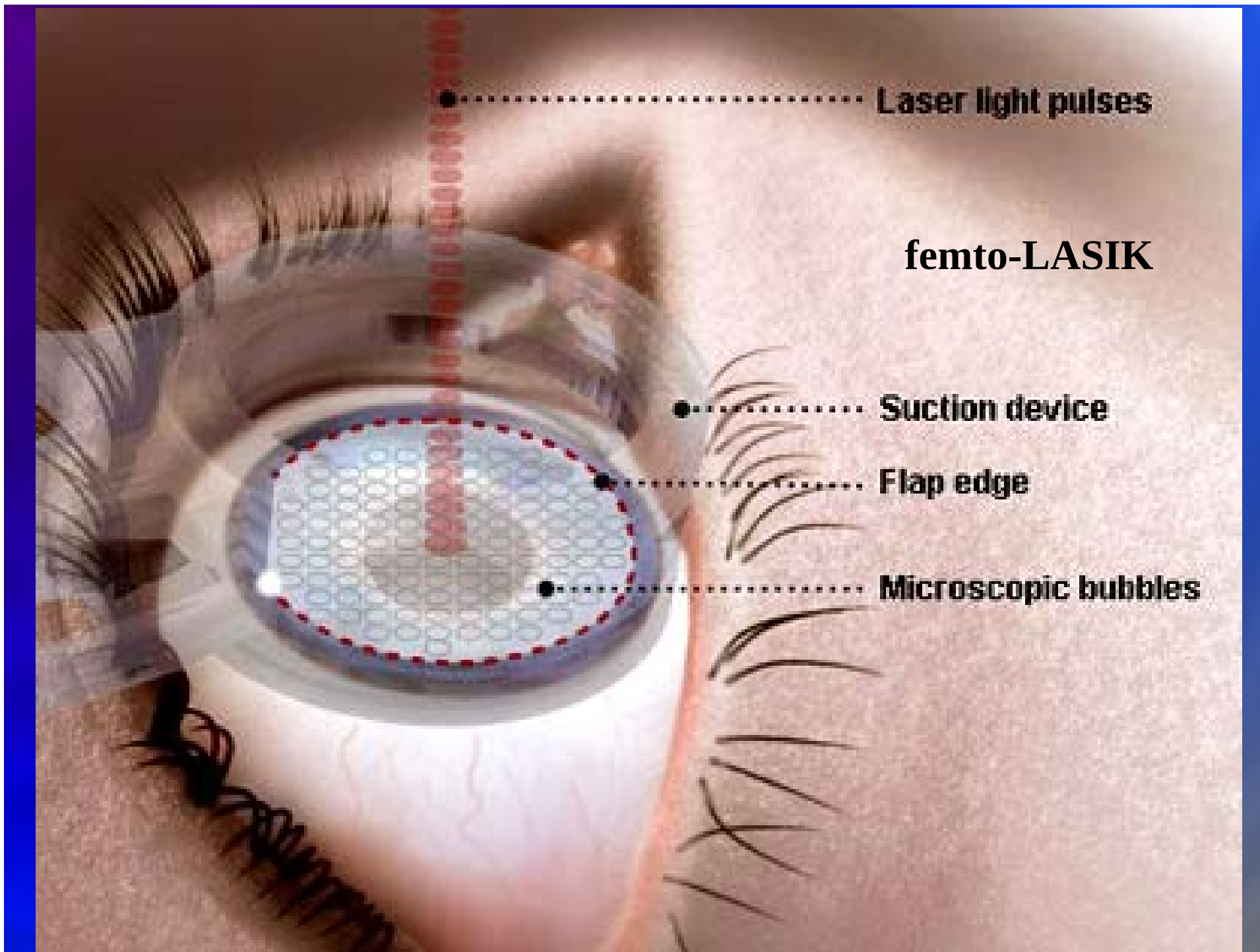
femto-LASIK

..... Laser light pulses

..... Suction device

..... Flap edge

..... Microscopic bubbles



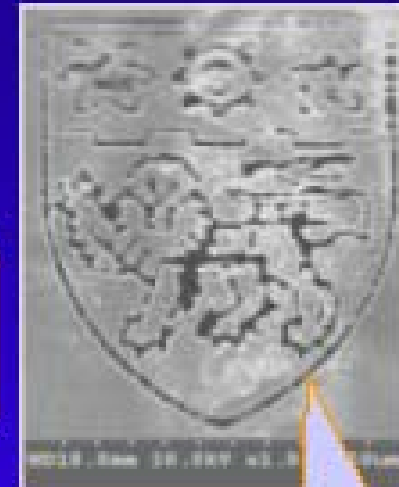
Femtosecond Laser Micromachining

SUB MICRON MACHINING

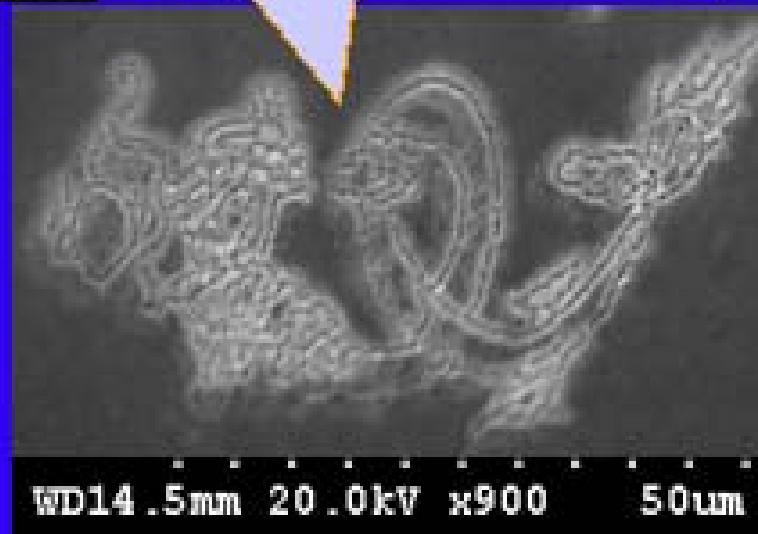


Merlion of
 $25\mu \times 100\mu$ on
solid copper

Dragon of $40\mu \times 60\mu$
on Platinum thin
film



Merlion of
 $50\mu \times 50\mu$ on
Copper film



Machining inside transparent materials

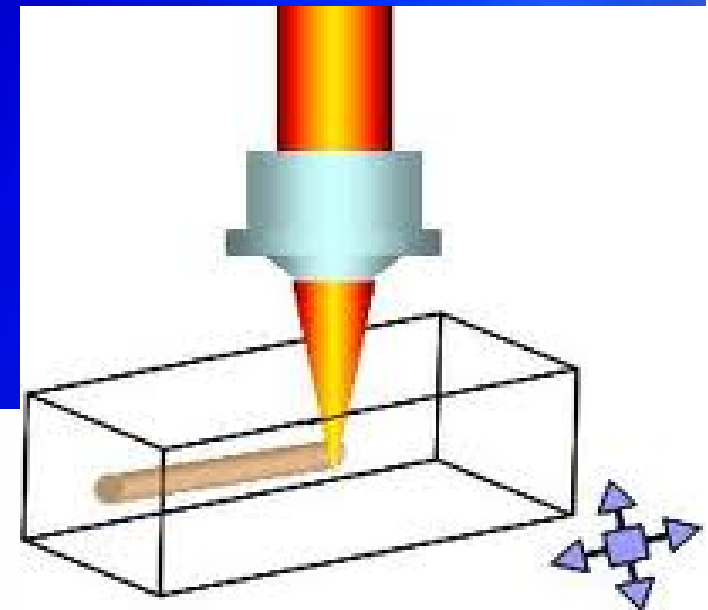
Focused probe beam

Transparent substrate



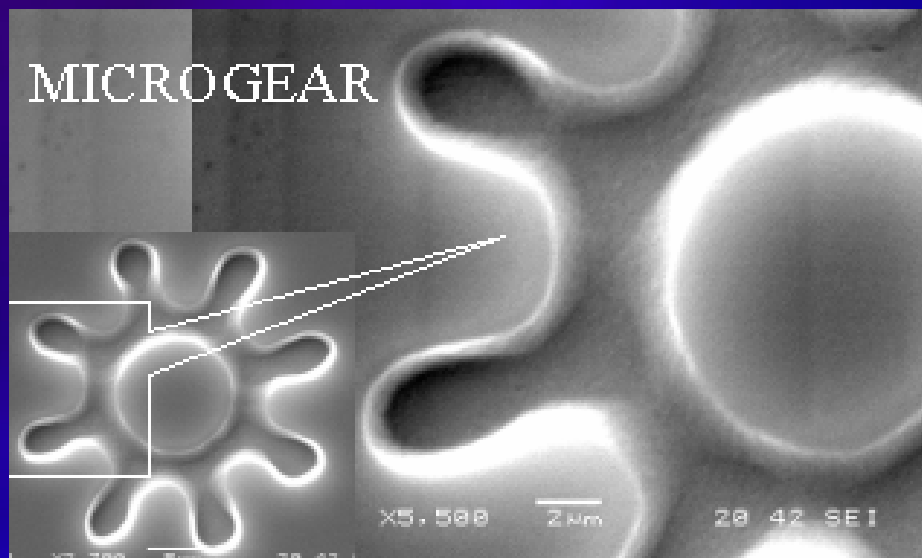
Waveguide written
with femtosecond laser

Probe beam guided
by waveguide



Femtosecond Laser Micromachining

Photomask Development



**Micro-gear (25µm X 25µm)
fabricated by lithography with
the mask fabricated by novel
system**

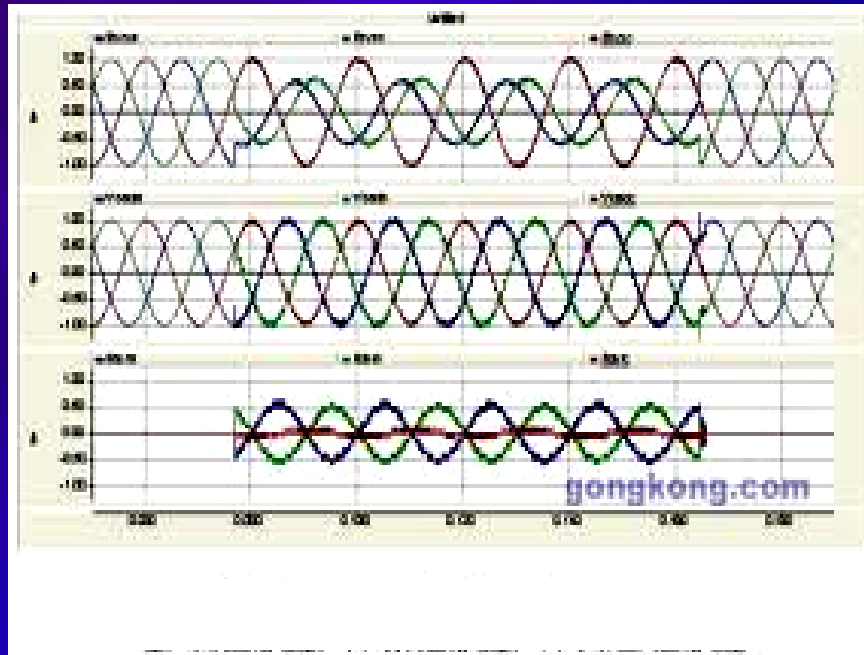
Inside surface machining



**Internal 3-D micromachining
micro eagle inside transparent
materials Using Femto-second
Laser**

Submicron machining

CW AND PULSED LASERS



E

Average power

Continuous Wave

t

Pulse duration

Peak Power

E

Pulsed Laser

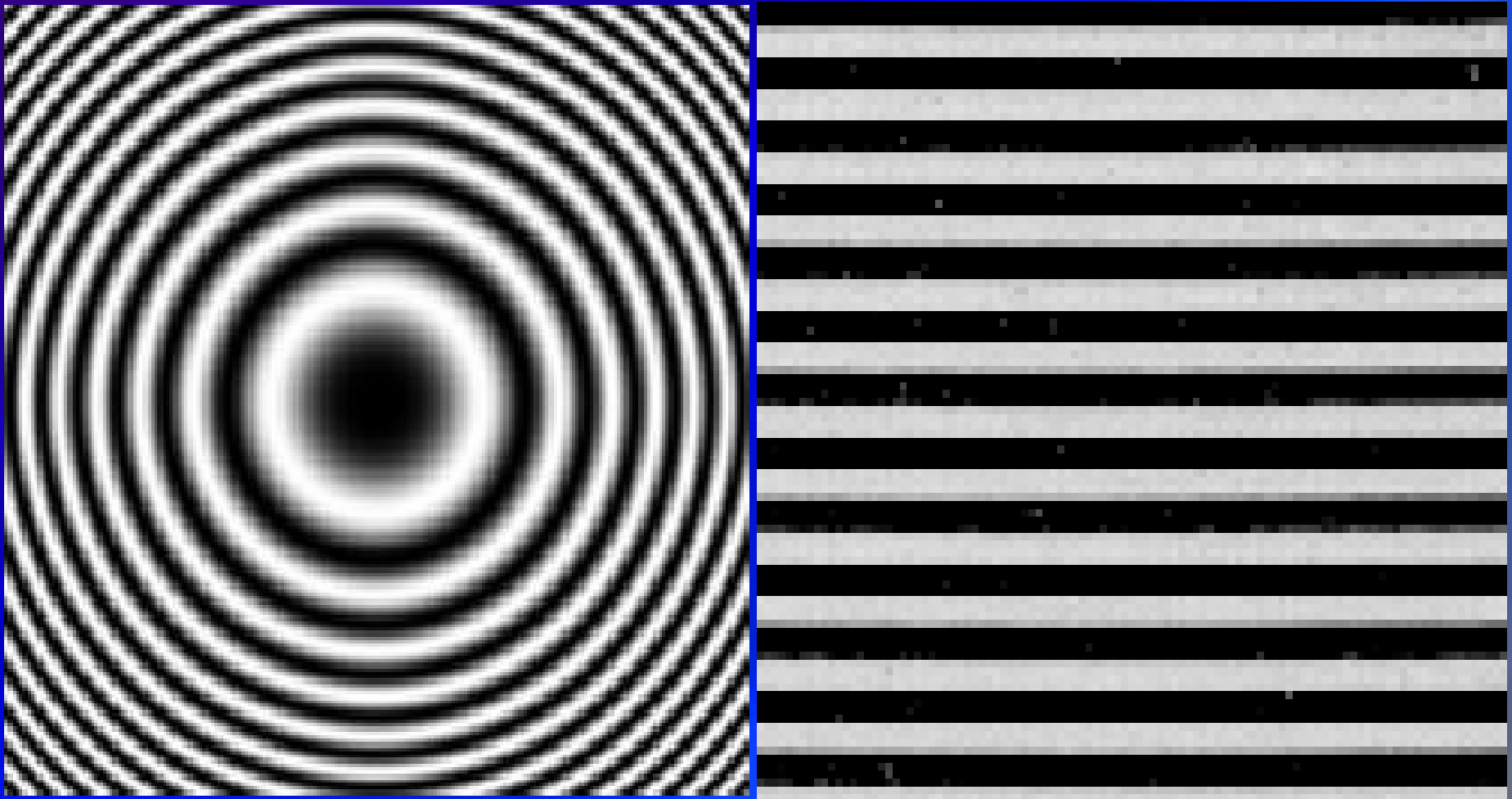
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Solution!

**Ultrafast Pulse Laser
Interference**

Interference is the phenomenon where two or more beams overlaps resulting in a series of bright & dark bands called ***fringes***



Laser Interference

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graph TD; A[Laser Interference] --> B[Interferometry]; A --> C[Bragg gratings on optical fibers]; A --> D[Micromachining]; B --> E[Spectroscopy]; B --> F[Metrology];
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Interferometry

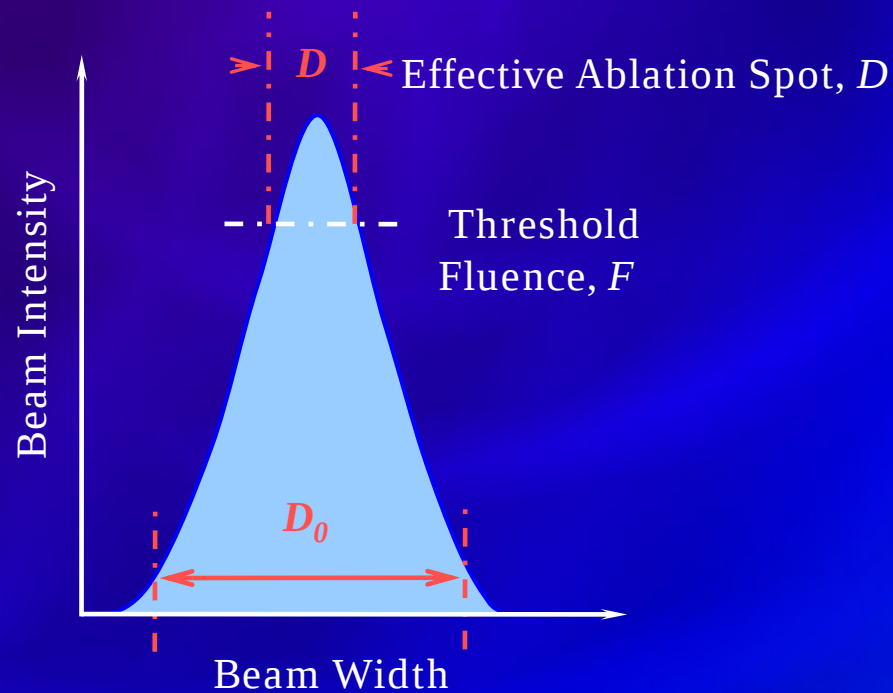
- Spectroscopy
- Metrology

Bragg gratings on
optical fibers

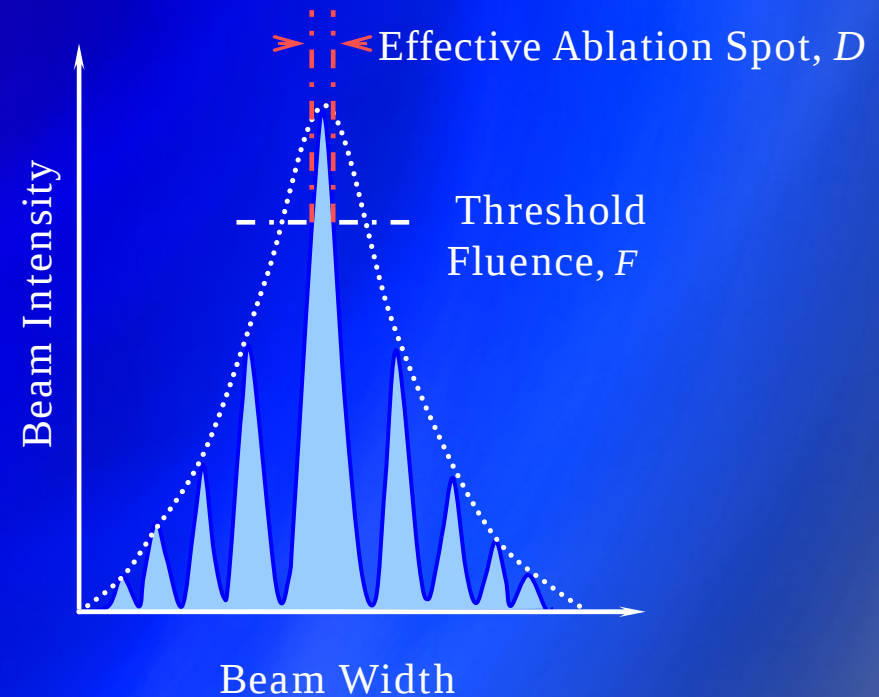
Micromachining

**How will the interfered laser
beam give better machining
performance?**

Conventional Non-Interfered Laser Beam vs. Interfered Laser Beam

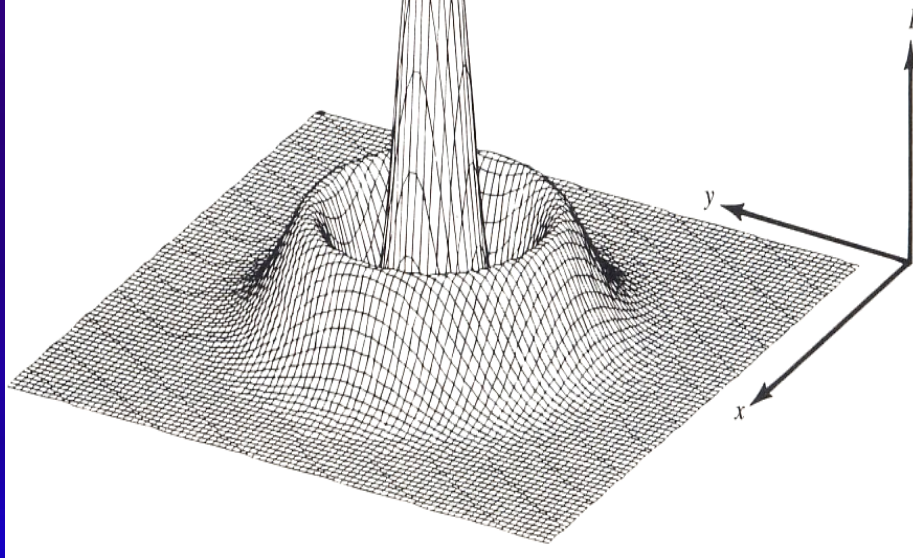


2D profile of the conventional
non-interfered Gaussian laser
beam

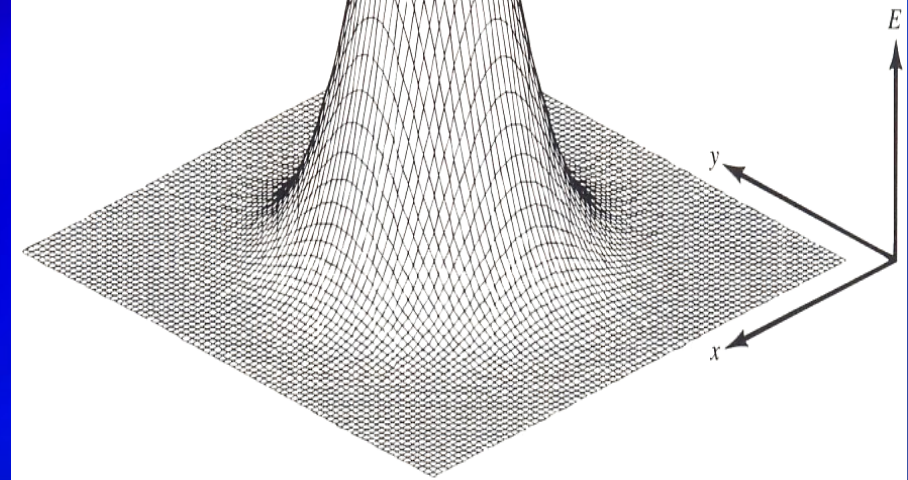


2D profile of the interfered
Gaussian-like laser beam

Interfered
beam



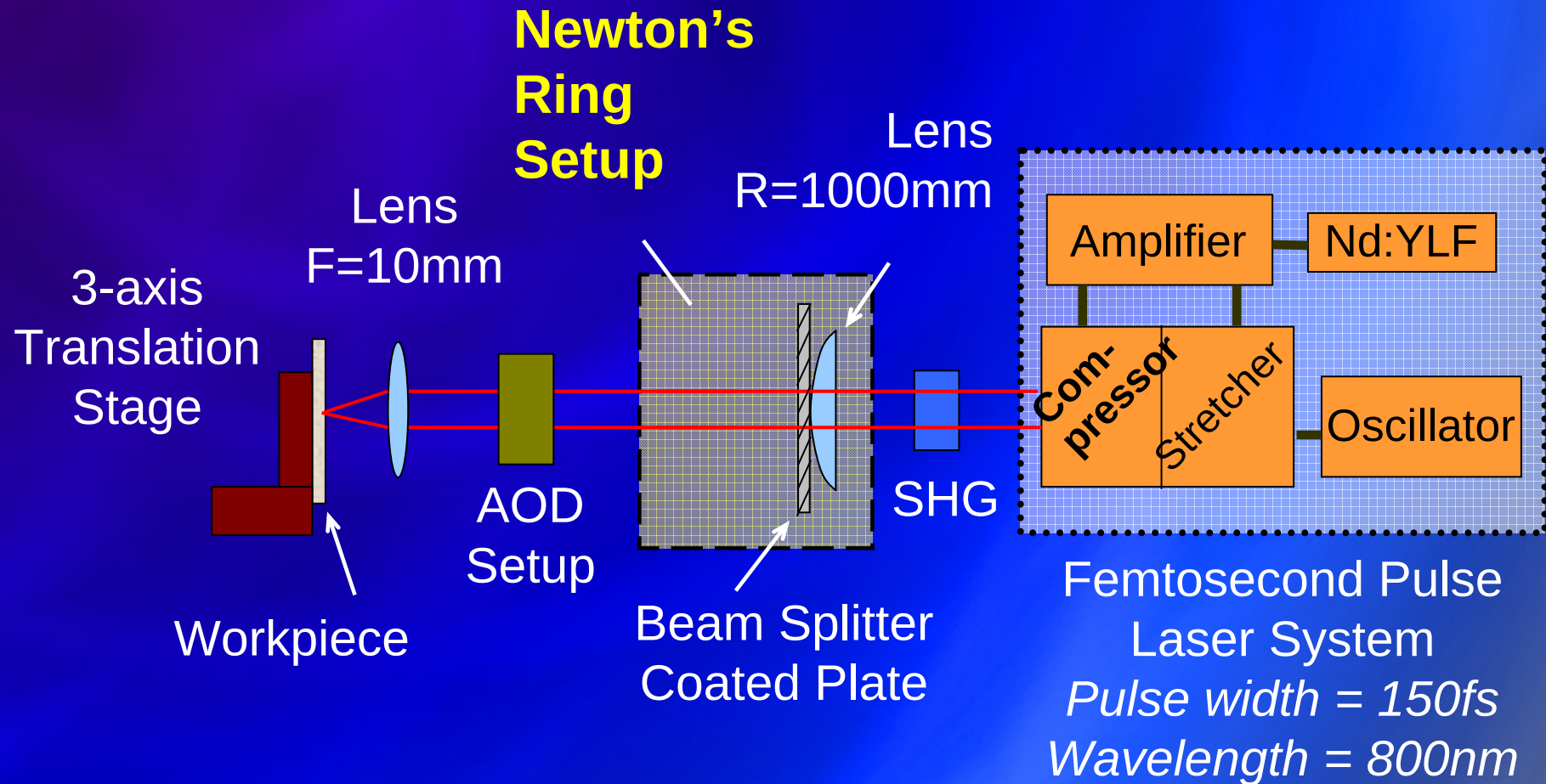
Direct
beam



3D profile of the **interfered**
Gaussian-like laser beam

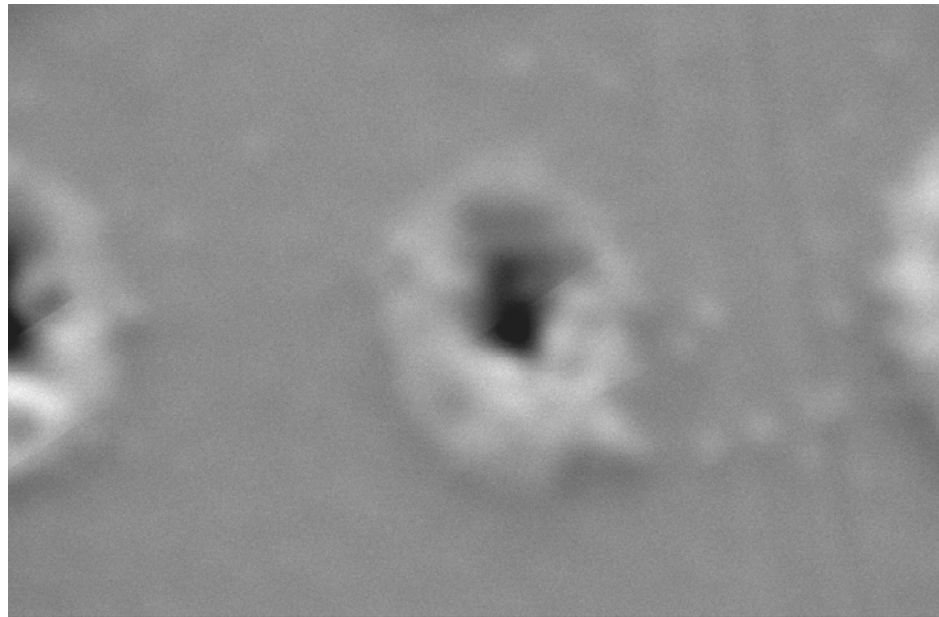
3D profile of the conventional
non-interfered Gaussian laser
beam

Experimental Set-up



Experimental Details:

Experimental Variables	Value
Pulse length	150fs
Wavelength	400nm
Repetition rate	1kHz
Environment	Ambient condition
Workpiece material	100nmCopper Film



20kV X22,000 1μm 26 33 SEI

Interfered beam

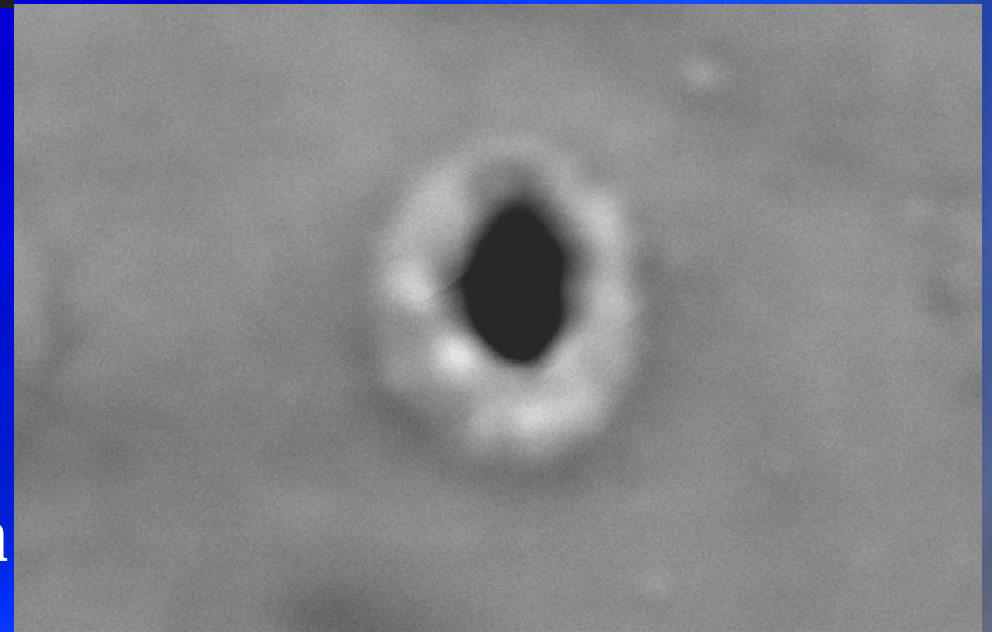
Hole diameter ☯ 300 nm

Beam energy: 5 nJ

Direct beam

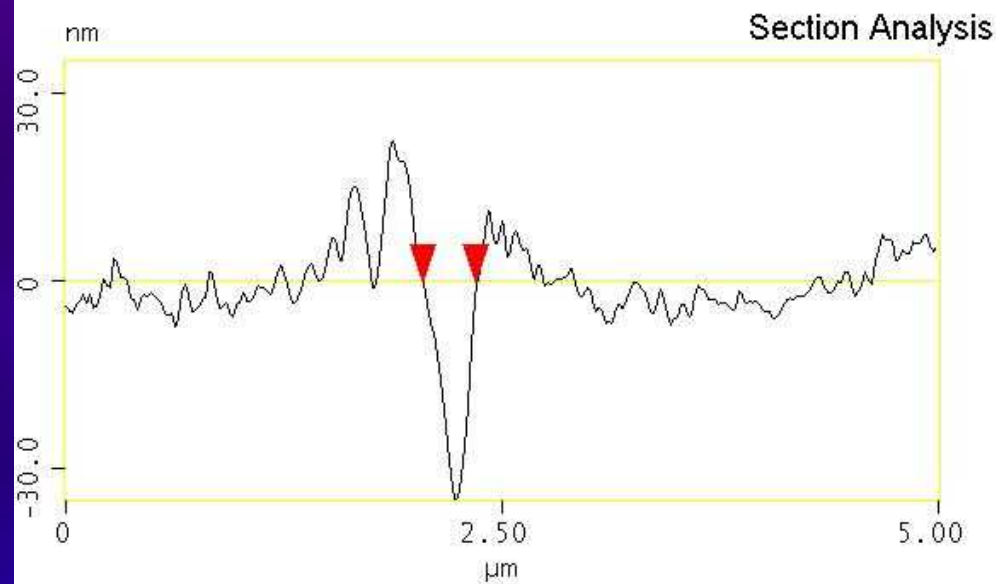
Hole diameter ☉ 1μm

Beam energy: 5 nJ

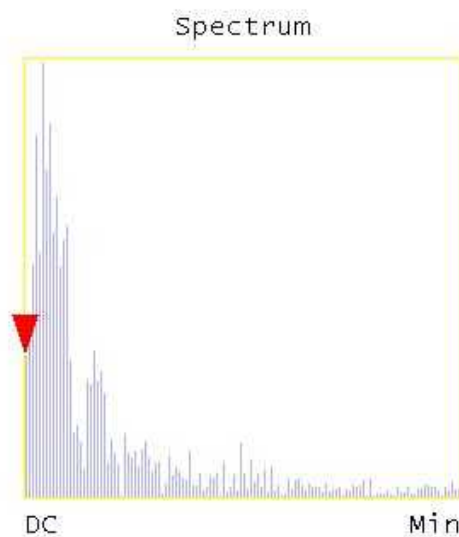
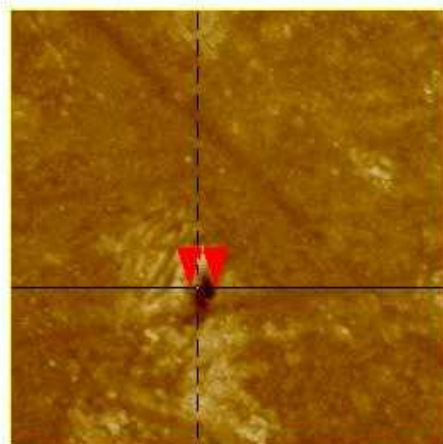


20kV X22,000 1μm 26 33 SEI

Cursor Marker Spectrum Zoom Center Line Offset Clear



L	292.97 nm
RMS	11.684 nm
lc	DC
Ra(lc)	8.499 nm
Rmax	41.147 nm
Rz	40.654 nm
Rz Cnt	2
Radius	305.80 nm
Sigma	5.579 nm



Surface distance	302.76 nm
Horiz distance(L)	292.97 nm
Vert distance	0.090 nm
Angle	0.018 °

Surface distance	
Horiz distance	
Vert distance	
Angle	

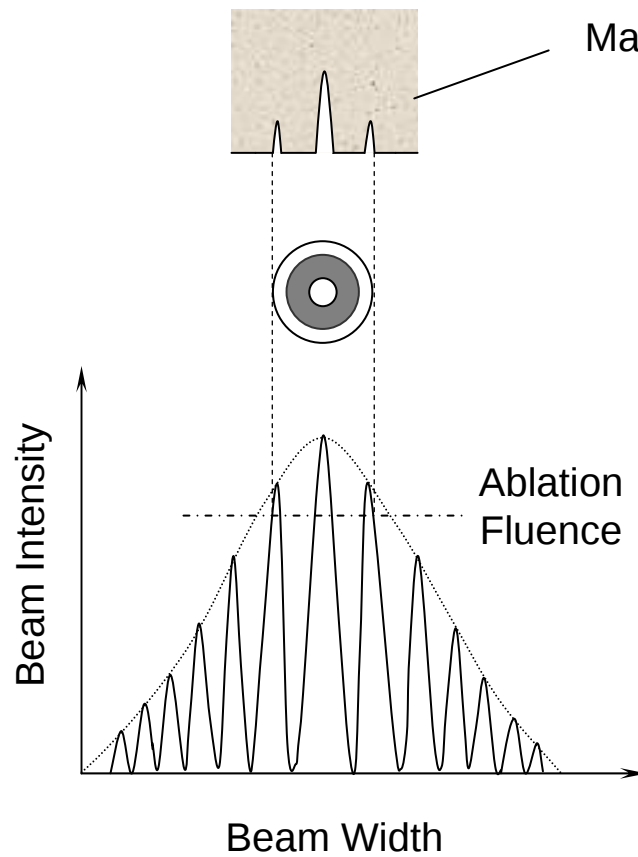
Surface distance	
Horiz distance	
Vert distance	
Angle	

Spectral period	DC
Spectral freq	0 Hz
Spectral RMS amp	0.004 nm

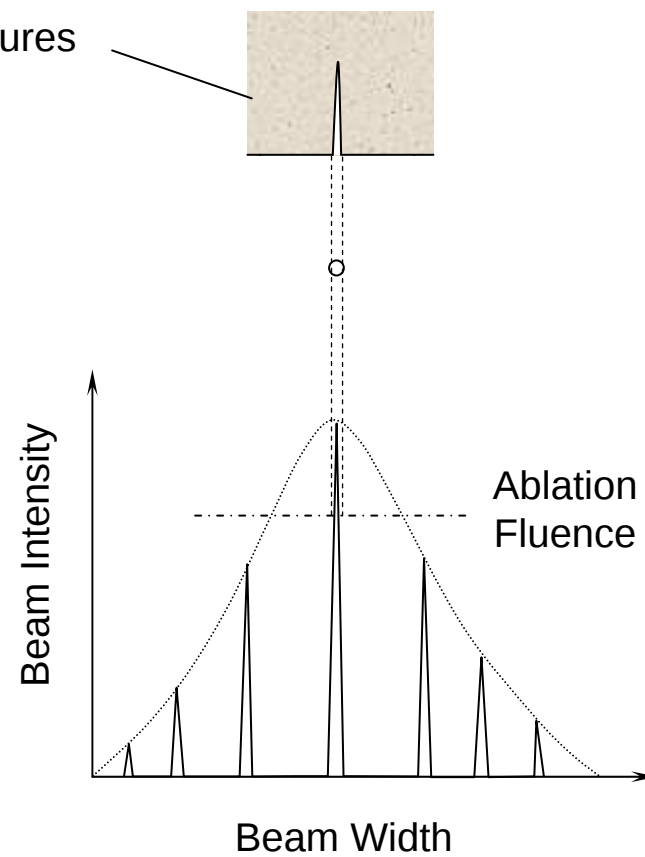
Cursor: moving Zoom: 1:1 Cen line: Off Offset: Off

Plans for Future Improvement

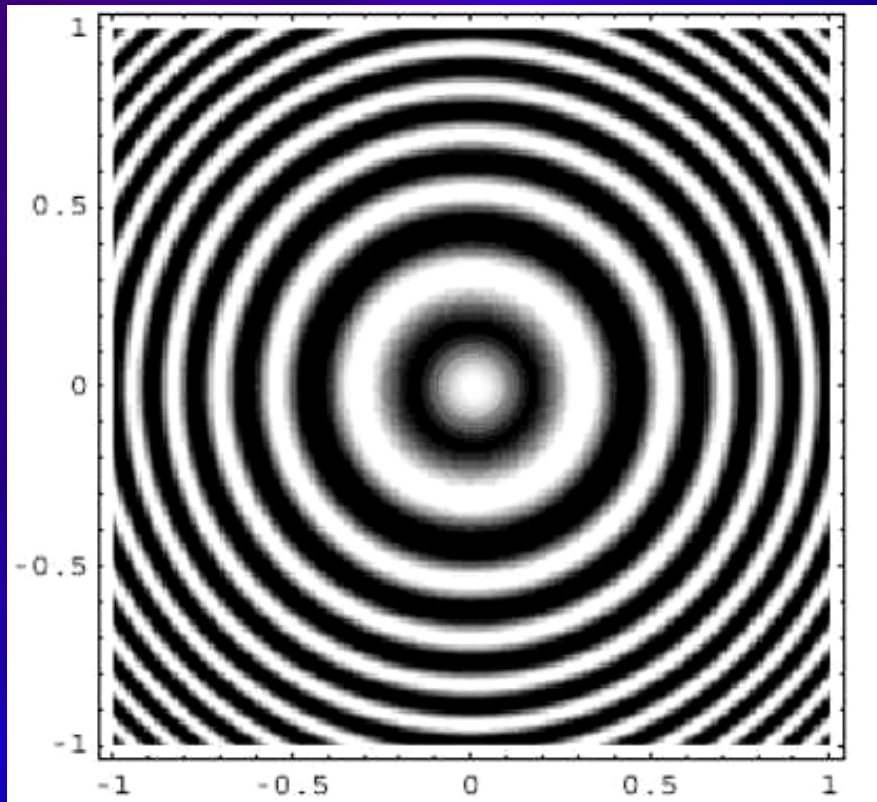
- to obtain finer features, sharper & finer fringes must be achieved. This may be done by:
 - * changing the curvature of the lens used
(the larger the curvature, the more fringes will be obtained, the denser the fringe pattern obtained)
 - * multiple interference (Fabry-Perot etalon)
 - * obtaining a Bessel beam (axicon)
 - * zone plate (multiple diffraction)



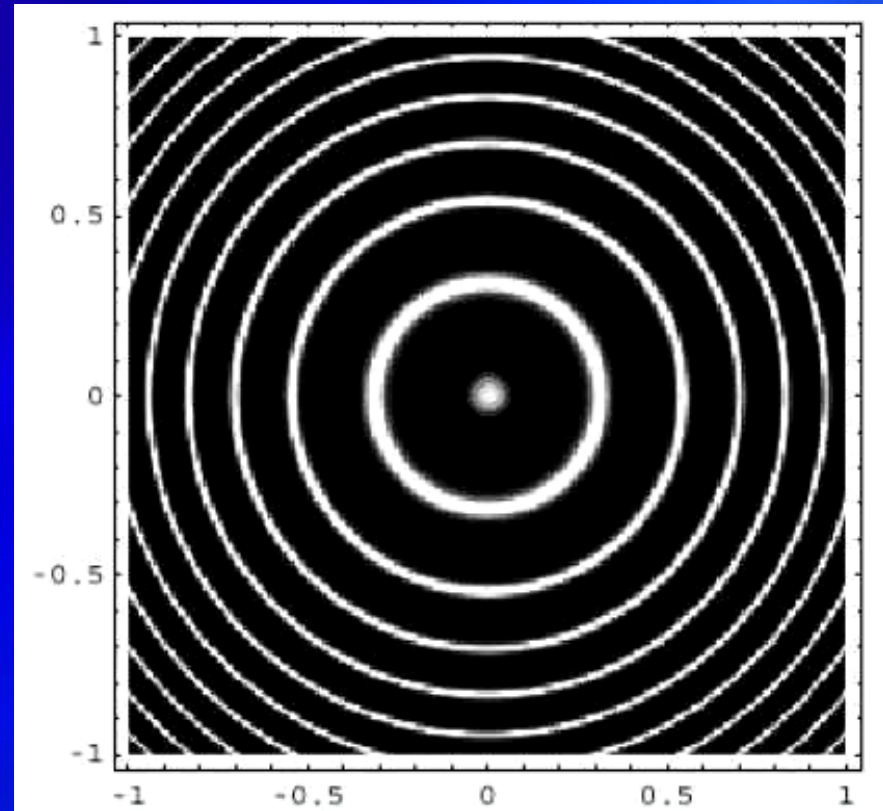
Beam profile of 2-beam
interference fringe



Beam profile of multiple
interference fringe



Two-beam interference
fringes



Multiple-beam
interference fringes

For constructive interference, when the 2 waves are in phase, the total intensity is proportional to $(E_1 + E_2)^2$

$$I_{total} \propto E_{total}^2 = (E_0 + E_0)^2 = 4E_0^2 \rightarrow I_{total} = 4I_0$$

Hence , 2 constructively interfered beams will give us light of **four(4) times** the intensity of either wave.



Alpha 1000/S

Output Specifications

Model	Standard	Picosecond Extension
Repetition rate [kHz]	1	
Wavelength [nm]	800 ± 20 (1)	
Pulse duration	< 100 fs (2)	< 1.5 ps (3)
Energy per pulse	800 µJ up to 2 mJ (4)	> 600 µJ
Pulse-to-pulse stability (% rms)	< 1.3	
Pre-pulse contrast ratio	> 500 : 1	
Post-pulse contrast ratio	> 100 : 1	
Typical picosecond contrast	> 1,000 : 1 @ 1 ps > 10,000 : 1 @ 5 ps > 100,000 : 1 @ 10 ps	
Typical time-bandwidth product	1.5 x Fourier-transform limit	
Beam profile before compressor	Gaussian	
Typical M ²	< 1.3	
Pump system	YLF 12 W @ 527 nm	

The threshold of a material can be calculated from the equation:

$$F_{th} \approx \frac{\Omega \rho \lambda}{4\pi k A}$$

where,

Ω = latent heat of evaporation by unit mass

ρ = density of the material

λ = wavelength of laser light

k = extinction coefficient of the material

A = absorptivity of the material

Calculated ablation threshold at laser wavelength of 400nm

Material	Latent Heat of Evaporation Ω	Density ρ	Extinction Coefficient at 400nm k	Absorptivity A	Threshold Value F_{th}
Platinum	2405 J/g	21.45 g/cm ³	2.84 cm ⁻¹	48%	120 mJ/cm ²
Gold	1738 J/g	19.30 g/cm ³	4.56 cm ⁻¹	20%	117 mJ/cm ²
Copper	4796 J/g	8.96 g/cm ³	2.21 cm ⁻¹	84%	72 mJ/cm ²

$$\begin{aligned}\text{Coherence Length} &= \frac{\lambda^2}{2\Delta\lambda} \\ &= \frac{800^2}{2(10)} = 32 \times 10^3 \text{ nm} \\ &= 32 \mu\text{m}\end{aligned}$$

where,

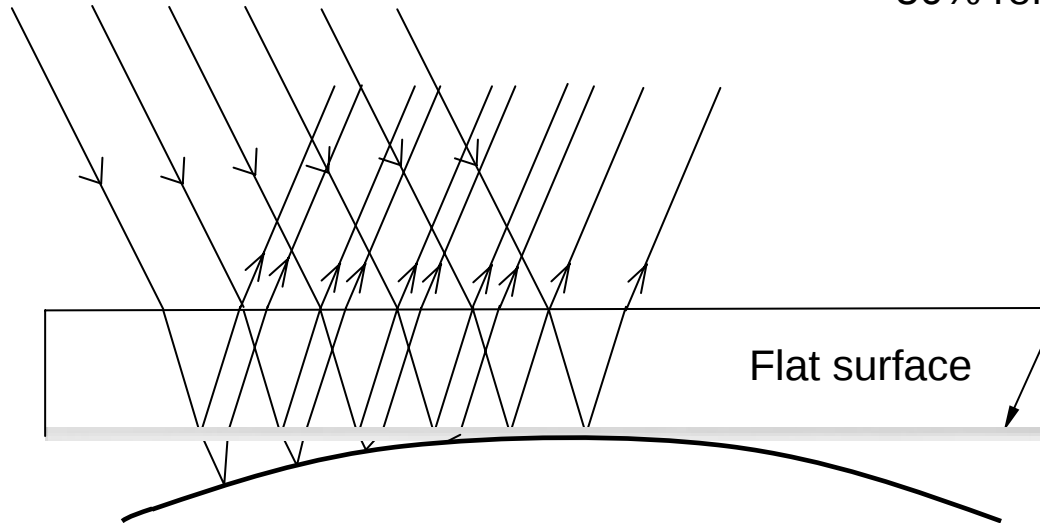
λ = laser wavelength in nm

$\Delta\lambda$ = laser bandwidth in nm

Newton's Ring Setup

Incoming collimated light

Birefringent coated surface
50% reflection; 50% transmission

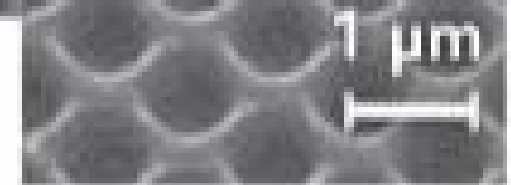
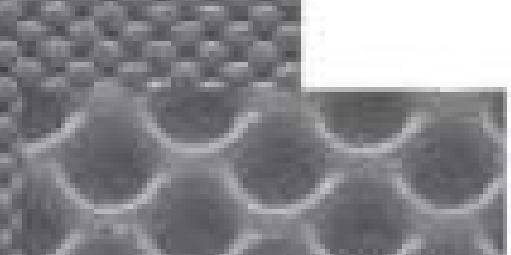
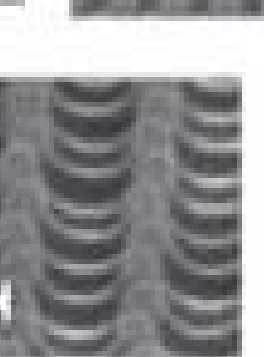
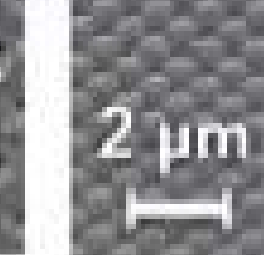
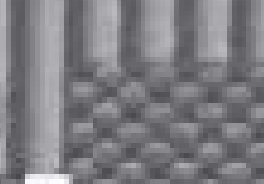
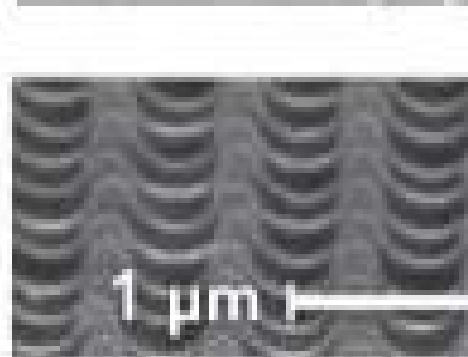
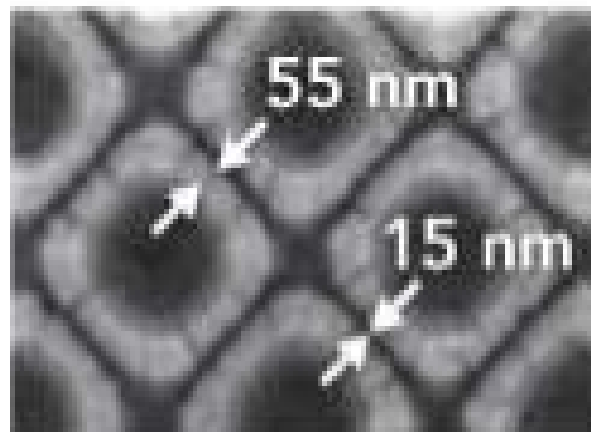
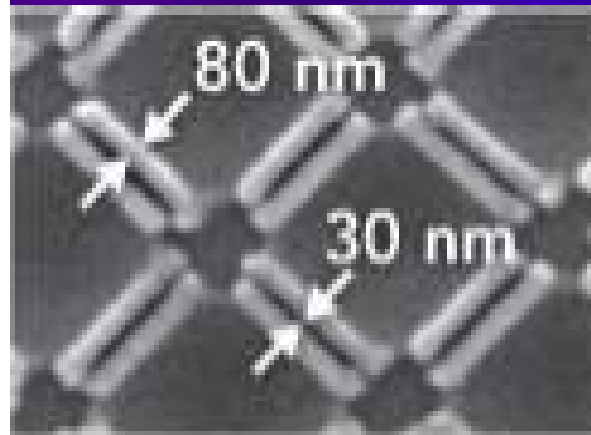


Flat surface

100% reflective curved mirror surface
Radius, $R=1000\text{mm}$

Results:

- 300nm holes were drilled using the interfered laser beam on the 100nm thick Cu film compared to the 1 μ m holes drilled with the conventional non-interfered laser beam at the same beam energy and machining parameters.
- This is equivalent to a 300% decrement in feature, a substantial reduction and improvement in feature size.



Source: Laser Laboratorium Göttingen e.V.



The layers of the organic solar cell are structured by means of ultra-short pulse laser. Source: 3D-Micromac.

Applications:

- drilling of microvias in the semicon industry
- micro-drilling of microscale fluidic devices such as ink-jet printer nozzles and drug-delivery systems
- direct writing on mask for lithographic applications
- microsurgery & non-intrusive surgical techniques
- the potential is limitless as the quest for miniaturization is endless!!

Thank you